

# PUMD13-Q

# NPN/PNP resistor-equipped double transistor; R1 = 4.7 k $\Omega$ , R2 = 47 k $\Omega$

25 October 2021

Product data sheet

# 1. General description

NPN/PNP double Resistor-Equipped Transistor (RET) in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package.

#### 2. Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- · Simplifies circuit design
- · Reduces component count
- Reduces pick and place costs
- Qualified according to AEC-Q101 and recommended for use in automotive applications

# 3. Applications

- Low current peripheral driver
- · Control of IC inputs
- · Replaces general-purpose transistors in digital applications

#### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Per transistor;	Per transistor; for the PNP transistor (TR2) with negative polarity where applicable							
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-	50	V	
I <sub>O</sub>	output current			-	-	100	mA	
R1	bias resistor 1		[1]	3.3	4.7	6.1	kΩ	
R2/R1	bias resistor ratio		[1]	8	10	12		

[1] See section "Test information" for resistor calculation and test conditions.



#### NPN/PNP resistor-equipped double transistor; R1 = 4.7 k $\Omega$ , R2 = 47 k $\Omega$

# 5. Pinning information

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	GND1	GND (emitter) TR1		O1 I2 GND2
2	I1	input (base) TR1		
3	O2	output (collector) TR2	6 5 4	R1 R2
4	GND2	GND (emitter) TR2		TR2
5	12	input (base) TR2		TR1 R2 R1
6	01	output (collector) TR1	☐1 ☐2 ☐3 TSSOP6 (SOT363)	GND1 I1 O2 006aaa143

# 6. Ordering information

**Table 3. Ordering information** 

Type number	Package					
	Name	Description	Version			
PUMD13-Q		plastic, surface-mounted package; 6 leads; 0.65 mm pitch; 2.1 mm x 1.25 mm x 0.95 mm body	SOT363			

## 7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PUMD13-Q	3%1

[1] % = placeholder for manufacturing site code

NPN/PNP resistor-equipped double transistor; R1 = 4.7 k $\Omega$ , R2 = 47 k $\Omega$ 

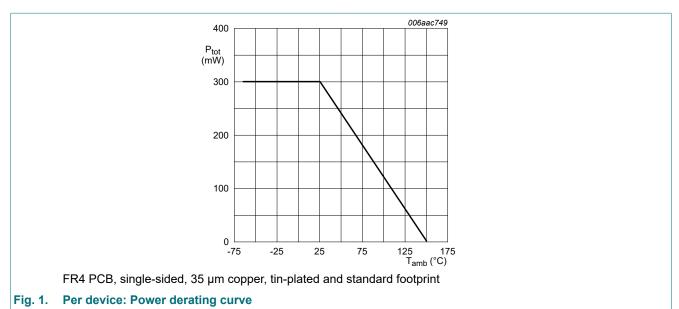
# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transist	or; for the PNP transistor (TR	(2) with negative polarity where applic	able	'		
V <sub>CBO</sub>	collector-base voltage	open emitter		-	50	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	50	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	5	V
V <sub>I</sub>	input voltage	positive (input voltage TR1)		-	30	V
		negative (input voltage TR1)		-	-5	V
		positive (input voltage TR2)		-	5	V
		negative (input voltage TR2)		-	-30	V
Io	output current			-	100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	200	mW
Per device	<u>'</u>			'	'	_
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	300	mW
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-65	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



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## 9. Thermal characteristics

#### **Table 6. Thermal characteristics**

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor	er transistor						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	625	K/W
Per device	Per device						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	417	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

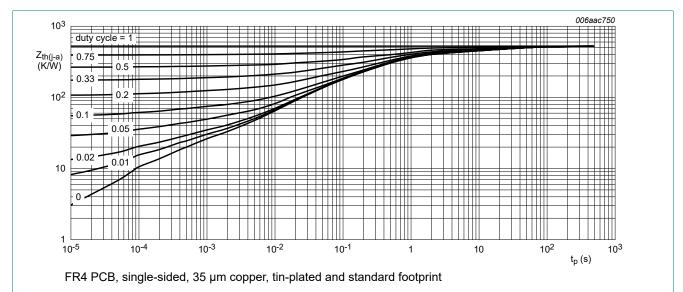


Fig. 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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# 10. Characteristics

#### **Table 7. Characteristics**

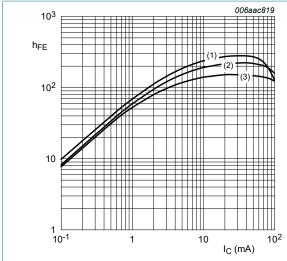
 $T_{amb}$  = 25 °C, unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transist	tor; for the PNP transistor (	TR2) with negative polarity where appl	icable				
V <sub>(BR)CBO</sub>	collector-base breakdown voltage	I <sub>C</sub> = 100 μA; I <sub>E</sub> = 0 A		50	-	-	V
$V_{(BR)CEO}$	collector-emitter breakdown voltage	$I_C = 2 \text{ mA}; I_B = 0 \text{ A}$		50	-	-	V
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = 50 \text{ V}; I_{E} = 0 \text{ A}$		-	-	100	nA
I <sub>CEO</sub>	collector-emitter cut-off	V <sub>CE</sub> = 30 V; I <sub>B</sub> = 0 A		-	-	1	μA
	current	V <sub>CE</sub> = 30 V; I <sub>B</sub> = 0 A; T <sub>j</sub> = 150 °C		-	-	5	μA
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = 5 V; I <sub>C</sub> = 0 A		-	-	170	μΑ
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 5 V; I <sub>C</sub> = 10 mA		100	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = 5 \text{ mA}; I_B = 0.25 \text{ mA}$		-	-	100	mV
$V_{I(off)}$	off-state input voltage	V <sub>CE</sub> = 5 V; I <sub>C</sub> = 100 μA		-	0.6	0.5	V
V <sub>I(on)</sub>	on-state input voltage	V <sub>CE</sub> = 0.3 V; I <sub>C</sub> = 5 mA		1.3	0.9	-	V
R1	bias resistor 1		[1]	3.3	4.7	6.1	kΩ
R2/R1	bias resistor ratio		[1]	8	10	12	
TR1 (NPN)				·			
C <sub>c</sub>	collector capacitance	V <sub>CB</sub> = 10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz		-	-	2.5	pF
f <sub>T</sub>	transition frequency	V <sub>CE</sub> = 5 V; I <sub>C</sub> = 10 mA; f = 100 MHz	[2]	-	230	-	MHz
TR2 (PNP)				-			
C <sub>c</sub>	collector capacitance	$V_{CB}$ = -10 V; $I_{E}$ = 0 A; $i_{e}$ = 0 A; $f$ = 1 MHz		-	-	3	pF
f <sub>T</sub>	transition frequency	V <sub>CE</sub> = -5 V; I <sub>C</sub> = -10 mA; f = 100 MHz	[2]	-	180	-	MHz

<sup>[1]</sup> See section "Test information" for resistor calculation and test conditions.

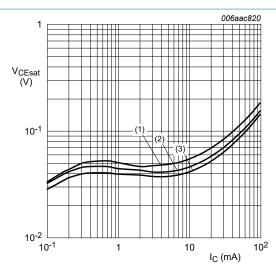
<sup>[2]</sup> Characteristics of built-in transistor

#### NPN/PNP resistor-equipped double transistor; R1 = 4.7 k $\Omega$ , R2 = 47 k $\Omega$



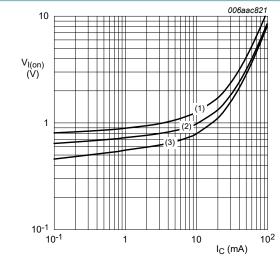
V<sub>CE</sub> = 5 V (1) T<sub>amb</sub> = 100 °C (2) T<sub>amb</sub> = 25 °C (3) T<sub>amb</sub> = -40 °C

TR1 (NPN): DC current gain as a function of Fig. 3. collector current; typical values



 $I_{C}/I_{B} = 20$ (1)  $T_{amb} = 100 \, ^{\circ}C$ (2)  $T_{amb} = 25 \, ^{\circ}C$ (3)  $T_{amb} = -40 \, ^{\circ}C$ 

Fig. 4. TR1 (NPN): Collector-emitter saturation voltage as a function of collector current; typical values



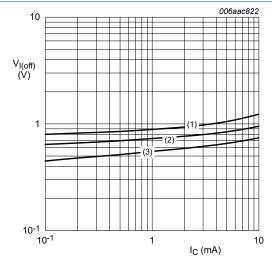
 $V_{CE}$  = 0.3 V

(1) T<sub>amb</sub> = -40 °C

(2) T<sub>amb</sub> = 25 °C

(3)  $T_{amb} = 100 \, ^{\circ}C$ 

Fig. 5. TR1 (NPN): On-state input voltage as a function | Fig. 6. of collector current; typical values



 $V_{CE} = 5 V$ 

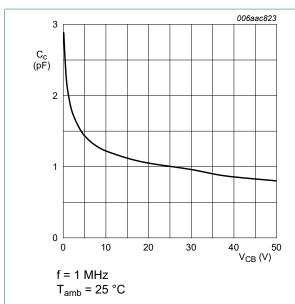
(1)  $T_{amb} = -40 \, ^{\circ}C$ 

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

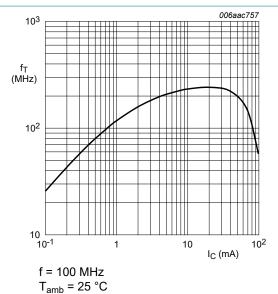
(3)  $T_{amb} = 100 \, ^{\circ}C$ 

TR1 (NPN): Off-state input voltage as a function of collector current; typical values

#### NPN/PNP resistor-equipped double transistor; R1 = 4.7 k $\Omega$ , R2 = 47 k $\Omega$

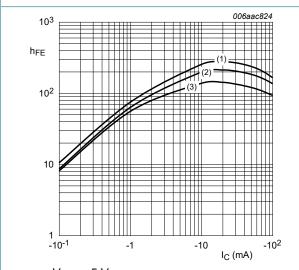


TR1 (NPN): Collector capacitance as a function Fig. 7. of collector-base voltage; typical values



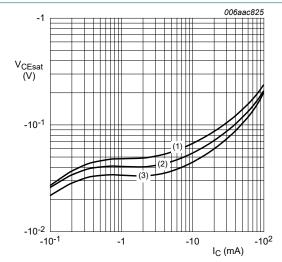
 $T_{amb}$  = 25 °C  $V_{CE}$  = 5 V

TR1 (NPN): Transition frequency as a function Fig. 8. of collector current; typical values of built-in transistor



 $V_{CE}$  = -5 V(1) T<sub>amb</sub> = 100 °C (2) T<sub>amb</sub> = 25 °C (3)  $T_{amb} = -40 \, ^{\circ}C$ 

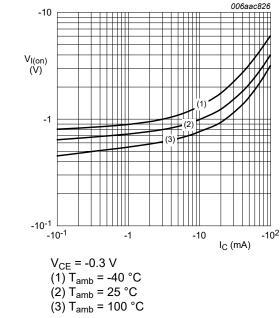
Fig. 9. TR2 (PNP): DC current gain as a function of collector current; typical values



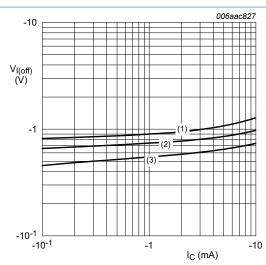
 $I_{\rm C}/I_{\rm B}=20$ (1)  $T_{amb}$  = 100 °C (2)  $T_{amb} = 25 \, ^{\circ}C$ (3)  $T_{amb} = -40 \, ^{\circ}C$ 

Fig. 10. TR2 (PNP): Collector-emitter saturation voltage as a function of collector current; typical values

#### NPN/PNP resistor-equipped double transistor; R1 = 4.7 k $\Omega$ , R2 = 47 k $\Omega$



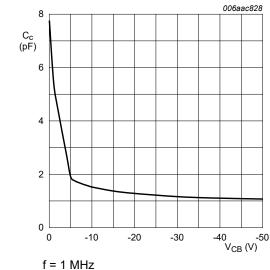
of collector current; typical values



V<sub>CE</sub> = -5 V (1) T<sub>amb</sub> = -40 °C (2) T<sub>amb</sub> = 25 °C

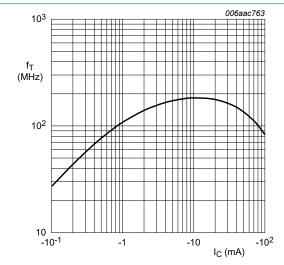
(3)  $T_{amb} = 100 \, ^{\circ}C$ 

Fig. 11. TR2 (PNP): On-state input voltage as a function | Fig. 12. TR2 (PNP): Off-state input voltage as a function of collector current; typical values



 $T_{amb}$  = 25 °C

Fig. 13. TR2 (PNP): Collector capacitance as a function of collector-base voltage; typical values



f = 100 MHz

 $T_{amb}$  = 25 °C

 $V_{CE} = -5 V$ 

Fig. 14. TR2 (PNP): Transition frequency as a function of collector current; typical values of built-in transistor

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NPN/PNP resistor-equipped double transistor; R1 = 4.7 k $\Omega$ , R2 = 47 k $\Omega$ 

## 11. Test information

#### **Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

#### **Resistor calculation**

· Calculation of bias resistor 1 (R1)

$$R1 = \frac{V(I12) - V(I11)}{I12 - I11}$$

· Calculation of bias resistor ratio (R2/R1)

$$\frac{R2}{R1} = \frac{V(I14) - V(I13)}{R1 \cdot (I14 - I13)} - 1$$

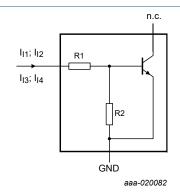


Fig. 15. NPN transistor: Resistor test circuit

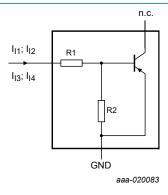


Fig. 16. PNP transistor: Resistor test circuit

#### **Resistor test conditions**

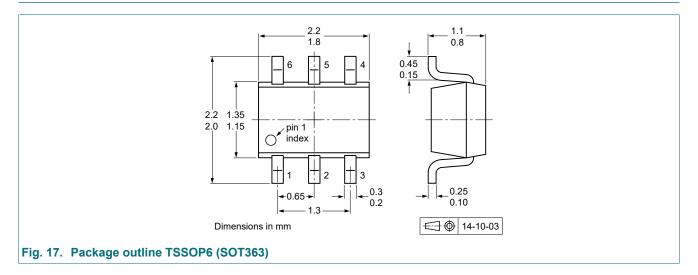
**Table 8. Resistor test conditions** 

Type number	Test conditions					
	I <sub>l1</sub>	I <sub>I2</sub>	I <sub>13</sub>	I <sub>14</sub>		
PUMD13-Q	90 μΑ	140 μΑ	-55 μA	-105 μA		
PUMD13-Q	-90 μA	-140 μΑ	55 μA	105 μΑ		

PUMD13-Q

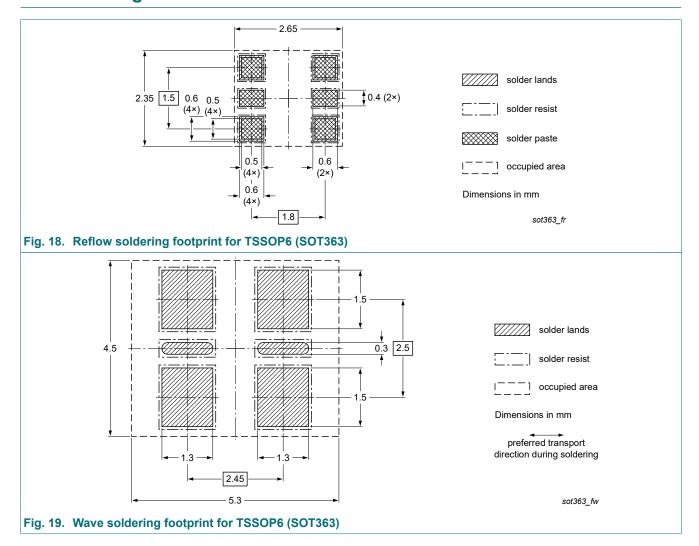
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# 12. Package outline



## NPN/PNP resistor-equipped double transistor; R1 = 4.7 k $\Omega$ , R2 = 47 k $\Omega$

# 13. Soldering



#### NPN/PNP resistor-equipped double transistor; R1 = 4.7 k $\Omega$ , R2 = 47 k $\Omega$

# 14. Revision history

#### Table 9. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PUMD13-Q v.1	20211025	Product data sheet	-	-

#### NPN/PNP resistor-equipped double transistor; R1 = 4.7 k $\Omega$ , R2 = 47 k $\Omega$

## 15. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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